

IN THE SPECIFICATION

Please replace the last paragraph starting on page 4 with the following text:

The etching of the natural oxide film ~~ilm~~ by hydrogen can be effected at temperatures above 900 °C at normal pressure, but, on the other hand, the speed of etching a silicon surface by hydrogen decreases rapidly when the temperature of heat treatment is lower than 1100 °C and the etching hardly occurs below 1080 °C.

Please insert the following text after the first full paragraph on page 7:

FIG. 3(a) is a drawing illustrating the surface condition of a silicon wafer before epitaxial growth.

FIG. 3(b) is a drawing illustrating the surface condition of a silicon wafer after epitaxial growth.

FIG. 4 is a schematic illustration of a light scattering type particle inspection apparatus.

Please replace the third full paragraph on page 7 with the following paragraph:

Nine p type silicon single crystal rods [[of]] having a diameter of 200 mm and [[of]] a resistivity of 0.01 Ωcm ~ 0.02 Ωcm were prepared, each rod having a different crystal defect density by varying the pulling-condition of the single crystal and/or the inside structure of the furnace. Then, the silicon single crystal rods were sliced to thin plates, and the ~~surface~~ surfaces of the sliced plates were

mirror polished to obtain mirror surface wafers 310 of plane orientation of (100).
(See FIGS. 3a and 3b.) The mirror surface wafers 310 obtained from each silicon single crystal rod were separated into two groups, one for preferential etching and another for vapor phase growth.

Please replace the last paragraph starting on page 7 with the following text:

The mirror surface wafers 310 for preferential etching were etched by said Secco solution, and surface defects 315 appearing as etch pits by the preferential etching were observed by means of a Normalski type differential interference microscope.

Please replace the second full paragraph on page 8 with the following text:

On the other hand, the mirror surface wafers 310 for vapor phase growth were placed in a vapor phase growth furnace 300 held to a hydrogen atmosphere 320, ~~and after~~ After three minutes of heat treatment at normal pressure and a temperature of 1050 °C, which results in removal of the natural oxide film 325 while hardly etching the surface of the silicon wafer, trichlorosilane (SiHCl₃) gas was supplied while keeping the temperature of 1050 °C to allow an epitaxial layer 340 of 4 μm thick and resistivity of 5 Ωcm to grow at normal pressure. Thus treated wafers were prepared as inspection object silicon wafers (405 in FIG. 4).

Please replace the third full paragraph on page 8 with the following text:

When said inspection object silicon wafers 405 for the purpose of detecting crystal defects, which are mirror surface wafers 310 with epitaxial layer 340 formed on the surface, were measured by a light scattering type particle inspection apparatus 400, crystal defects such as stacking faults_(SF) and dislocation defects having pits 350 and/or projections 360 were apparent on the surface of said inspection objects and detected as particles by detecting scattered light 415 generated by light source 410 with detector 420.